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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

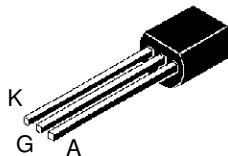
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

SENSITIVE GATE SCR

FEATURES

- $I_T(\text{RMS}) = 1.25\text{A}$
- $V_{\text{DRM}} = 200\text{V}$ to 800V
- Low $I_{\text{GT}} < 200 \mu\text{A}$



TO92
(Plastic)

DESCRIPTION

The X02xxxA series of SCRs uses a high performance TOP GLASS PNPN technology. These parts are intended for general purpose applications where low gate sensitivity is required.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_T(\text{RMS})$	RMS on-state current (180° conduction angle)	1.25	A
$I_T(\text{AV})$	Mean on-state current (180° conduction angle)	0.8	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	tp = 8.3 ms	A
		tp = 10 ms	
I^2t	I^2t Value for fusing	2.5	A^2s
dI/dt	Critical rate of rise of on-state current $I_G = 10 \text{ mA}$ $dI/dt = 0.1 \text{ A}/\mu\text{s}$.	30	$\text{A}/\mu\text{s}$
T_{stg} T_j	Storage and operating junction temperature range	- 40, + 150 - 40, + 125	$^\circ\text{C}$
TI	Maximum lead temperature for soldering during 10s at 2mm from case	260	$^\circ\text{C}$

Symbol	Parameter	Voltage				Unit
		B	D	M	N	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ\text{C}$ $R_{\text{GK}} = 1\text{K}\Omega$	200	400	600	800	V

X02xxxA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	150	°C/W
R _{th(j-l)}	Junction to leads for DC	60	°C/W

GATE CHARACTERISTICS (maximum values)

P_{G(AV)}= 0.2 W P_{GM} = 3 W (tp = 20 μs) I_{GM} = 1.2 A (tp = 20 μs)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Sensitivity			Unit
		02	03	05	
I _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MIN		20 20
			MAX	200 200	50
V _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MAX	0.8	
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ R _{GK} = 1 KΩ	T _j = 125°C	MIN	0.1	
V _{RGM}	I _{RG} = 10μA	T _j = 25°C	MIN	8	
t _{gd}	V _D =V _{DRM} I _{TM} = 3 x I _{T(AV)} dI _G /dt = 0.1A/μs I _G = 10mA	T _j = 25°C	TYP	0.5	
I _H	I _T = 50mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	5	
I _L	I _G =1mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	6	
V _{TM}	I _{TM} = 2.5A tp= 380μs	T _j = 25°C	MAX	1.45	
I _{DRM} I _{RRM}	V _D = V _{DRM} R _{GK} = 1 KΩ V _R = V _{RRM}	T _j = 25°C	MAX	5	
		T _j = 110°C	MAX	200	
dV/dt	V _D =67%V _{DRM} R _{GK} = 1 KΩ	T _j = 110°C	TYP	15 20 15	V/μs
t _q	I _{TM} = 3 x I _{T(AV)} V _R =35V dI/dt=10A/μs tp=100μs dV/dt=2V/μs V _D = 67%V _{DRM} R _{GK} = 1 KΩ	T _j = 110°C	MAX	100	

ORDERING INFORMATION

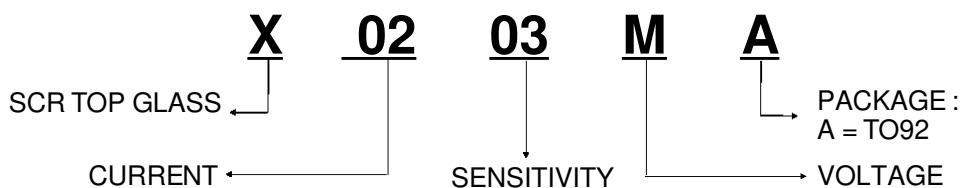


Fig.1 : Maximum average power dissipation versus average on-state current.

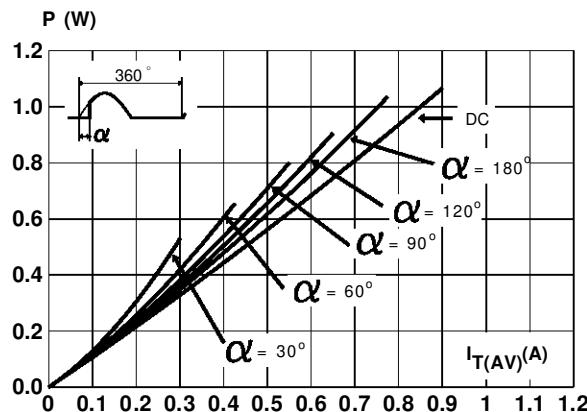


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Tlead).

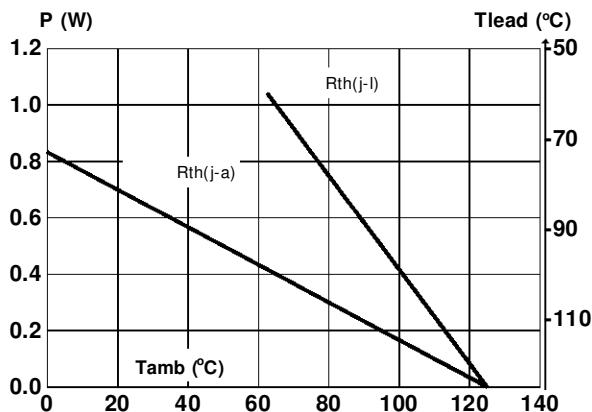


Fig.3 : Average on-state current versus lead temperature.

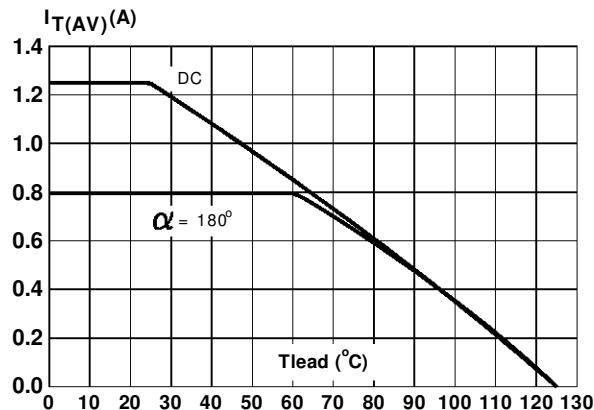


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

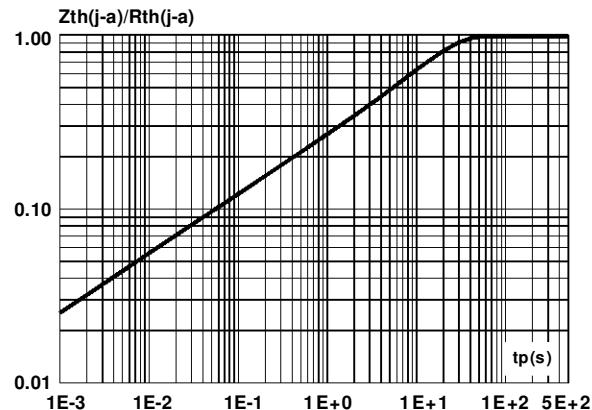


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

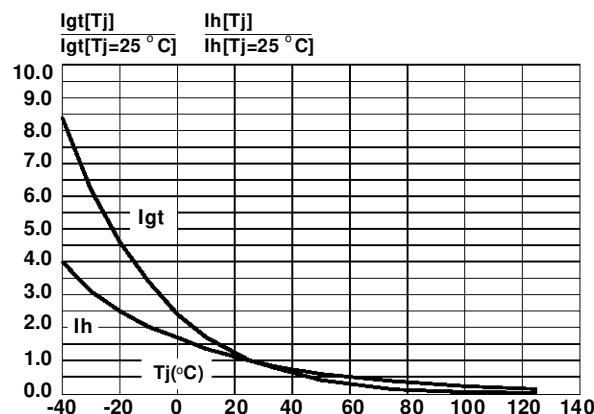
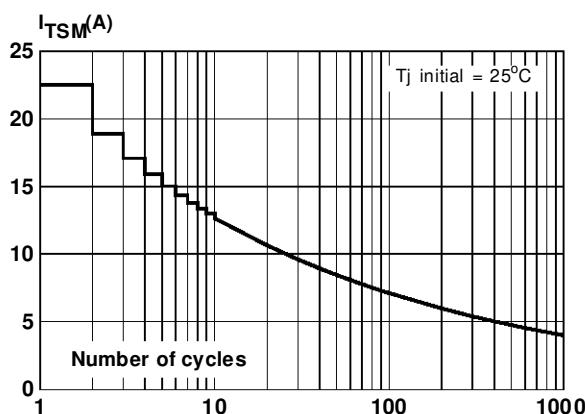


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.



X02xxxA

Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10\text{ms}$, and corresponding value of I^2t .

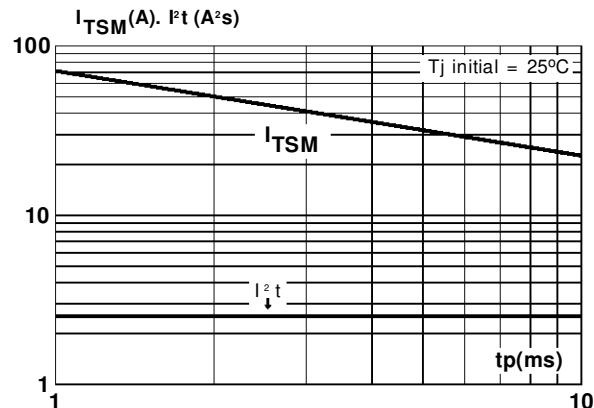
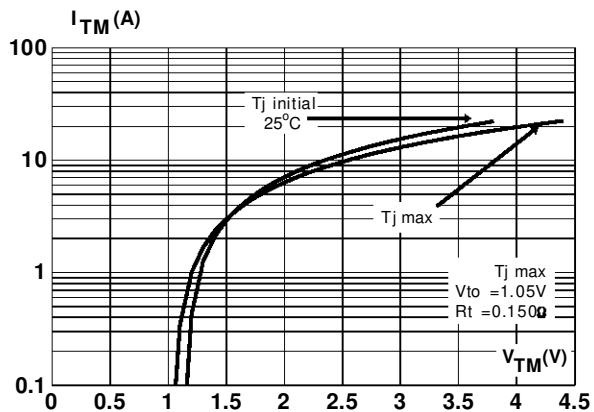


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA
TO92 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	1.35			0.053		
B			4.7			0.185
C	2.54			0.100		
D		4.4	4.8		0.173	0.189
E		12.7			0.500	
F			3.7			0.146
a			0.45			0.017

Marking : Type number

Weight : 0.2 g

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